2^{nd} Generation thinQ!™ SiC Schottky Diode

Product Summary

V_{DC}	600	V
Q_c	15	nC
I_F	6	A

Features

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery/ No forward recovery
- No temperature influence on the switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[1)] for target applications
- Breakdown voltage tested at 5mA[2)]

D^2PAK

thinQ! 2G Diode designed for fast switching applications like:

- CCM PFC
- Motor Drives

Type	Package	Marking	Pin 2	Pin 3
IDB06S60C	D^2PAK	D06S60C	C	A

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	I_F	T_C<135 °C	6	A
RMS forward current	$I_{F,RMS}$	f=50 Hz	9	
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	T_C=25 °C, t_p=10 ms	46	
Repetitive peak forward current	$I_{F,RM}$	T_j=150 °C, T_C=100 °C, D=0.1	24	
Non-repetitive peak forward current	$I_{F,max}$	T_C=25 °C, t_p=10 µs	210	
i^2t value	$\int i^2 dt$	T_C=25 °C, t_p=10 ms	10	A^2s
Repetitive peak reverse voltage	V_{RRM}		600	V
Diode ruggedness dv/dt	dv/dt	V_R=0…480V	50	V/ns
Power dissipation	P_{tot}	T_C=25 °C	52	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	2.9	K/W
Thermal resistance, junction - ambient	R_{thJA}	SMD version, device on PCB, minimal Footprint	-	-	62	
		SMD version, device on PCB, 6 cm^2 cooling area[3)]	-	35	-	
Soldering temperature, reflowsoldering @ 10sec	T_{sold}	reflow MSL1	-	-	260	°C

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Static characteristics						
DC blocking voltage	V_{DC}	I_R=0.08 mA	600	-	-	V
Diode forward voltage	V_F	I_F=6 A, T_j=25 °C	-	1.5	1.7	
		I_F=6 A, T_j=150 °C	-	1.7	2.1	
Reverse current	I_R	V_R=600 V, T_j=25 °C	-	0.7	80	µA
		V_R=600 V, T_j=150 °C	-	3	800	
AC characteristics						
Total capacitive charge	Q_c	V_R=400 V, $I_F \leq I_{F,max}$, di_F/dt=200 A/µs, T_j=150 °C	-	15	-	nC
Switching time[4)]	t_c		-	-	<10	ns
Total capacitance	C	V_R=1 V, f=1 MHz	-	280	-	pF
		V_R=300 V, f=1 MHz	-	35	-	
		V_R=600 V, f=1 MHz	-	35	-	

[1)] J-STD20 and JESD22

[2)] All devices tested under avalanche conditions, for a time periode of 5ms at 5mA.

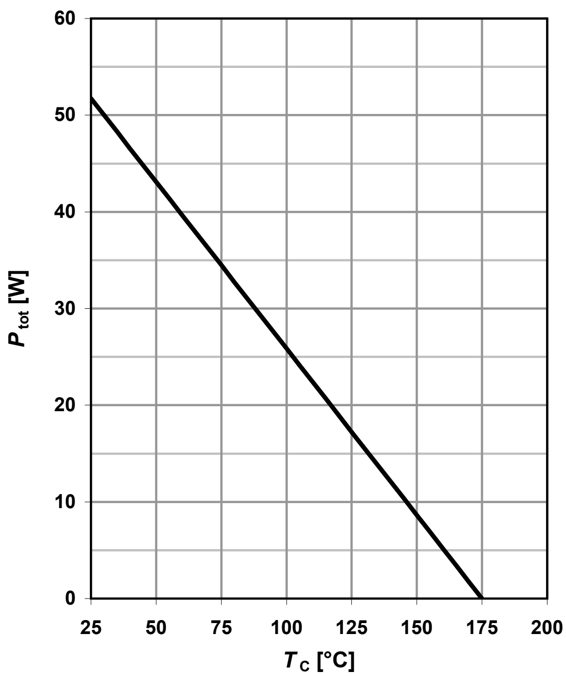
[3)] Device on 40mm*40mm*1.5mm epox PCB FR4 with 6cm^2 (one layer, 70µm thick) copper area for drain connection. PCB is vertikal with out blown air.

[4)] t_c is the time constant for the capacitive displacement current waveform (independent from T_j, I_{LOAD} and di/dt), different from t_{rr}, which is dependent on T_j, I_{LOAD}, di/dt. No reverse recovery time constant t_{rr} due to absence of minority carrier injection.

[5)] Only capacitive charge occuring, guaranteed by design.

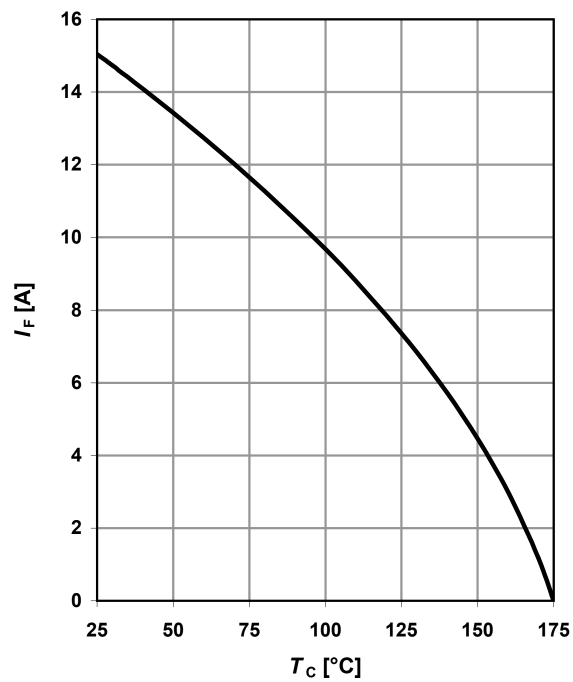
1 Power dissipation

P_{tot}=f(T_C)



2 Diode forward current

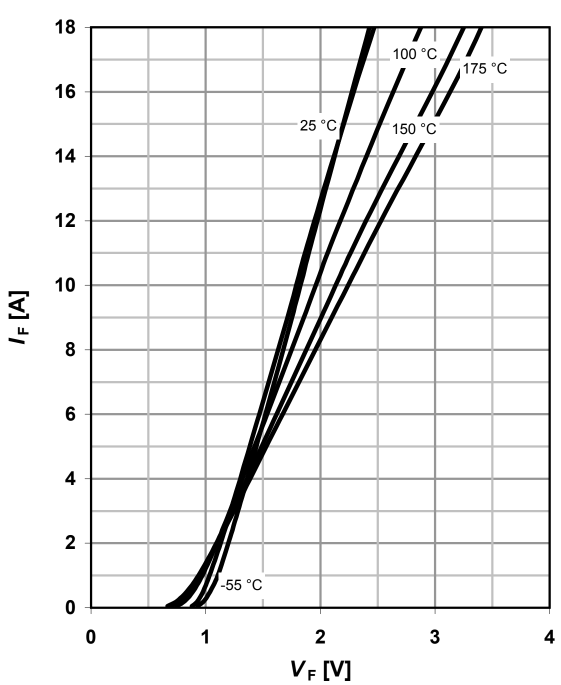
I_F=f(T_C); T_j≤175 °C



3 Typ. forward characteristic

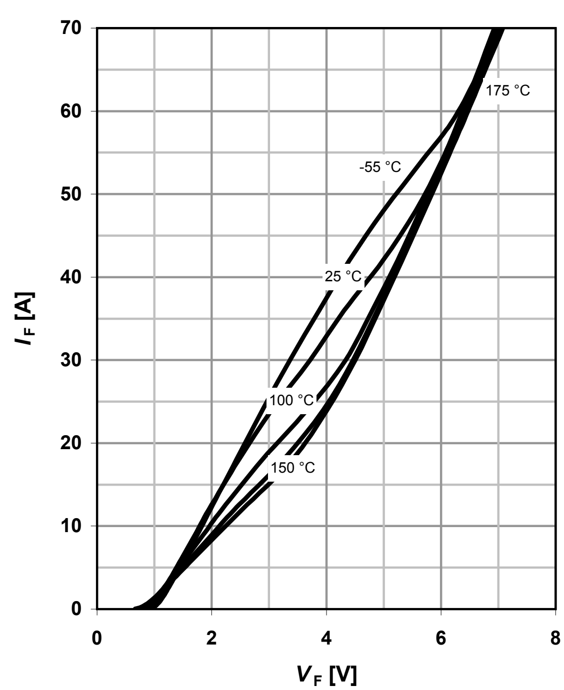
I_F=f(V_F); t_p=400 µs

parameter: T_j



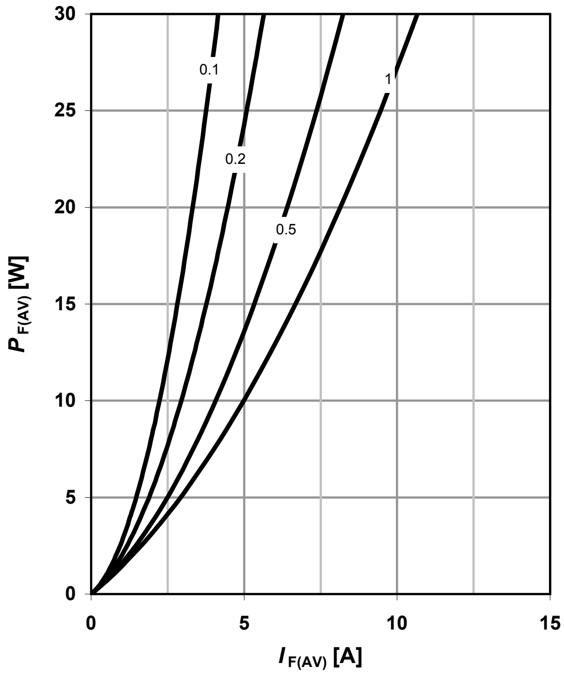
4 Typ. forward characteristic in surge current mode

I_F=f(V_F); t_p=400 µs; parameter T_j



5 Typ. forward power dissipation vs. average forward current

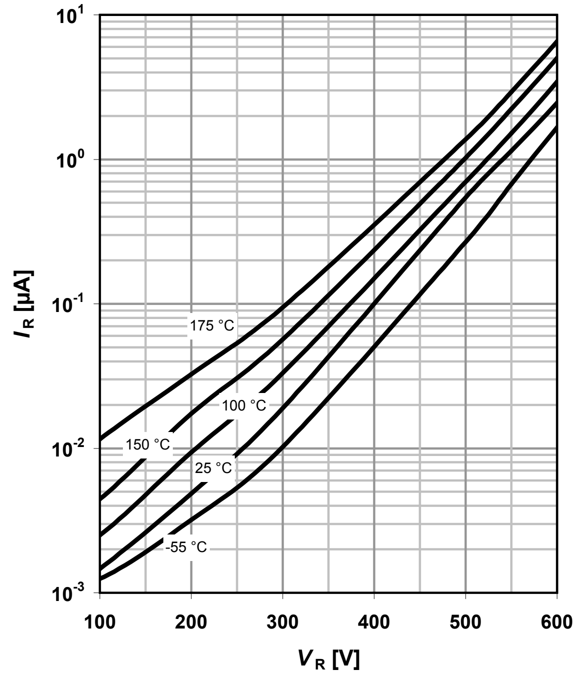
$P_{F,AV}$=f(I_F), T_C=100 °C, parameter: $D=t_p/T$



6 Typ. reverse current vs. reverse voltage

I_R=f(V_R)

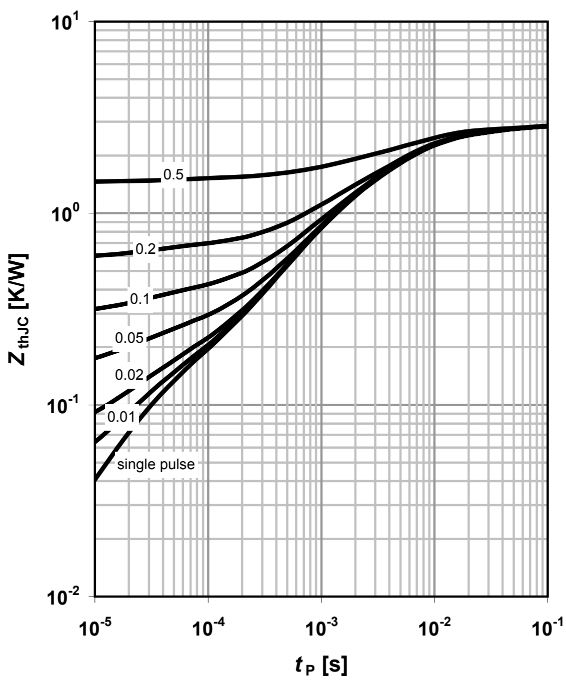
parameter: T_j



7 Transient thermal impedance

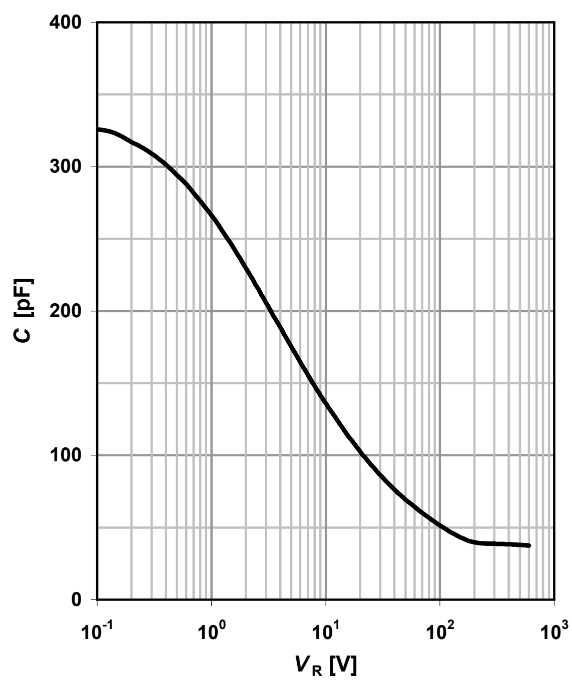
Z_{thJC}=f(t_p)

parameter: $D=t_p/T$



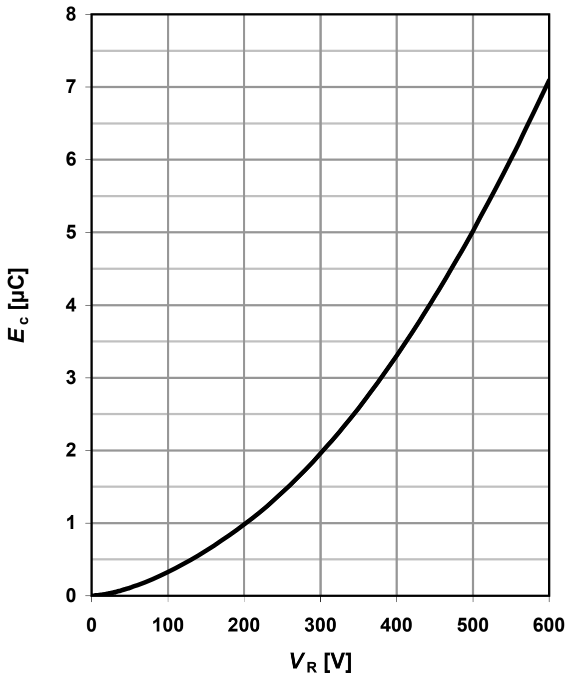
8 Typ. capacitance vs. reverse voltage

C=f(V_R); T_C=25 °C, f=1 MHz



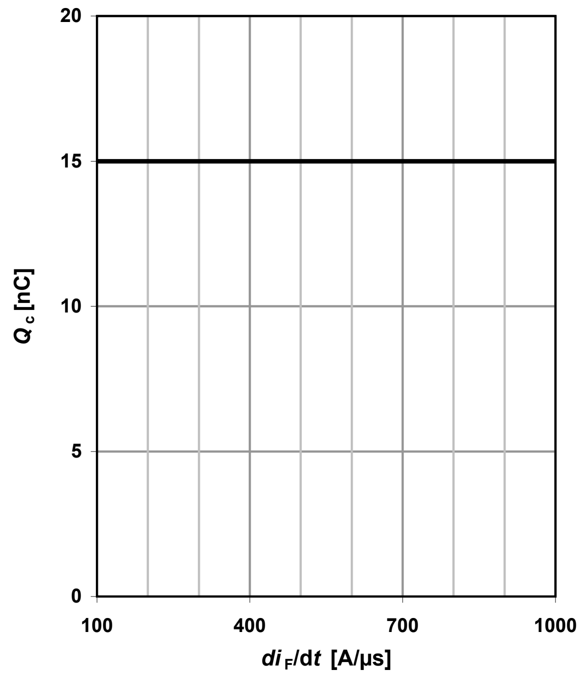
9 Typ. C stored energy

E_C=f(V_R)

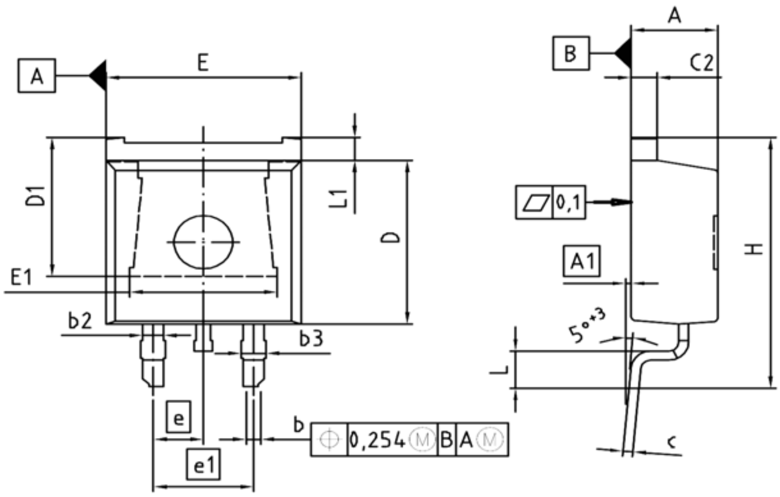


10 Typ. capacitance charge vs. current slope

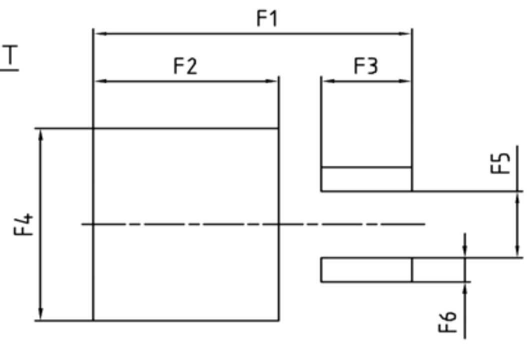
Q_C=f(di_F/dt)[5)]; T_j=150 °C; I_F≤$I_{F,max}$



PG-TO220-3-45 (D2Pak): Outline



FOOTPRINT



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.50	0.169	0.177
A1	0.00	0.20	0.000	0.008
b	0.72	0.85	0.028	0.033
b2	0.95	1.15	0.037	0.045
b3	0.95	1.45	0.037	0.057
c	0.50	0.65	0.020	0.026
c2	1.28	1.40	0.050	0.055
D	9.00	9.40	0.354	0.370
D1	7.60	8.00	0.299	0.315
E	9.80	10.00	0.386	0.394
E1	6.50	7.60	0.256	0.299
e	2.54		0.100	
e1	5.08		0.200	
N	2		2	
H	14.10		0.555	
L	1.40	2.40	0.055	0.094
L1	1.20	1.40	0.047	0.055
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	3.65	3.85	0.144	0.152
F6	1.25	1.45	0.049	0.057

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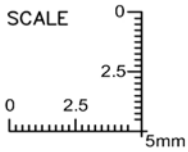
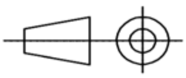
SCALE



EUROPEAN PROJECTION



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